

FEATURES

Enhanced system-level ESD performance per IEC 61000-4-x

Low power operation

5 V operation

1.4 mA per channel maximum at 0 Mbps to 2 Mbps

4.3 mA per channel maximum at 10 Mbps

34 mA per channel maximum at 90 Mbps

3.3 V operation

0.9 mA per channel maximum at 0 Mbps to 2 Mbps

2.4 mA per channel maximum at 10 Mbps

20 mA per channel maximum at 90 Mbps

Bidirectional communication

3.3 V/5 V level translation

High temperature operation: 105°C

High data rate: dc to 90 Mbps (NRZ)

Precise timing characteristics

2 ns maximum pulse width distortion

2 ns maximum channel-to-channel matching

High common-mode transient immunity: >25 kV/μs

Output enable function

16-lead SOIC wide body, RoHS-compliant package

Safety and regulatory approvals

UL recognition: 2500 V rms for 1 minute per UL 1577

CSA Component Acceptance Notice 5A

VDE Certificate of Conformity

DIN V VDE V 0884-10 (VDE V 0884-10): 2006-12

V_{IORM} = 560 V peak

APPLICATIONS

General-purpose multichannel isolation

SPI/data converter isolation

RS-232/RS-422/RS-485 transceivers

Industrial field bus isolation

GENERAL DESCRIPTION

The ADuM3400/ADuM3401/ADuM3402¹ are 4-channel digital isolators based on the Analog Devices, Inc., *iCoupler*® technology. Combining high speed CMOS and monolithic air core transformer technology, these isolation components provide outstanding performance characteristics superior to alternatives such as optocoupler devices.

iCoupler devices remove the design difficulties commonly associated with optocouplers. Typical optocoupler concerns regarding uncertain current transfer ratios, nonlinear transfer functions, and temperature and lifetime effects are eliminated with the simple *iCoupler* digital interfaces and stable performance characteristics. The need for external drivers and other discrete components is eliminated with these *iCoupler* products. Furthermore, *iCoupler* devices consume one-tenth to one-sixth the power of optocouplers at comparable signal data rates.

The isolators provide four independent isolation channels in a variety of channel configurations and data rates (see the Ordering Guide). All models operate with the supply voltage on either side ranging from 3.0 V to 5.5 V, providing compatibility with lower voltage systems as well as enabling a voltage translation functionality across the isolation barrier. The isolators have a patented refresh feature that ensures dc correctness in the absence of input logic transitions and during power-up/power-down conditions.

In comparison to the ADuM1400/ADuM1401/ADuM1402 isolators, the ADuM3400/ADuM3401/ADuM3402 isolators contain various circuit and layout changes to provide increased capability relative to system-level IEC 61000-4-x testing (ESD/burst/surge). The precise capability in these tests for either set of isolators is strongly determined by the design and layout of the user board or module. For more information, see the AN-793 Application Note, *ESD/Latch-Up Considerations with iCoupler Isolation Products*.

FUNCTIONAL BLOCK DIAGRAMS

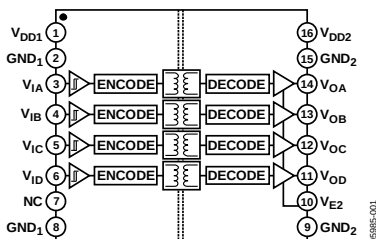


Figure 1. ADuM3400 Functional Block Diagram

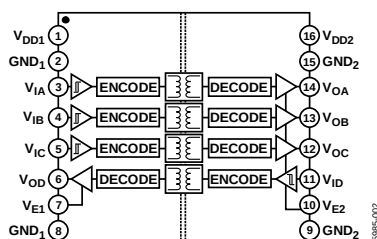


Figure 2. ADuM3401 Functional Block Diagram

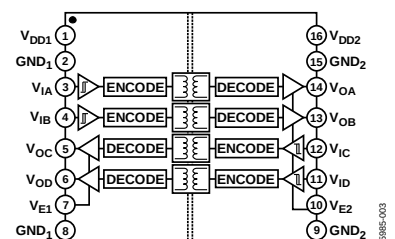


Figure 3. ADuM3402 Functional Block Diagram

¹ Protected by U.S. Patents 5,952,849; 6,873,065; 6,903,578; and 7,075,329.

Rev. F

Document Feedback

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TABLE OF CONTENTS

Features	1
Applications	1
General Description	1
Functional Block Diagrams	1
Revision History	2
Specifications	3
Electrical Characteristics—5 V Operation	3
Electrical Characteristics—3.3 V Operation	6
Electrical Characteristics—Mixed 5 V/3.3 V or 3.3 V/5 V Operation	8
Package Characteristics	12
Regulatory Information	12
Insulation and Safety-Related Specifications	12
DIN V VDE V 0884-10 (VDE V 0884-10) Insulation Characteristics	13
Recommended Operating Conditions	13

Absolute Maximum Ratings	14
ESD Caution	14
Pin Configurations and Function Descriptions	15
Typical Performance Characteristics)	18
Application Information	20
PC Board Layout	20
System-Level ESD Considerations and Enhancements	20
Propagation Delay-Related Parameters	20
DC Correctness and Magnetic Field Immunity	20
Power Consumption	21
Insulation Lifetime	22
Outline Dimensions	23
Ordering Guide	23

REVISION HISTORY

7/2017—Rev. E to Rev. F

Changes to Logic High Output Voltages Parameter and Logic Low Output Voltages Parameter, Table 1	3
Changes to Logic High Output Voltages Parameter and Logic Low Output Voltages Parameter, Table 2	6
Changes to Logic High Output Voltages Parameter and Logic Low Output Voltages Parameter, Table 3	9

7/2016—Rev. D to Rev. E

Changes to Features Section and General Description Section	1
Changes to Electrical Characteristics—3.3 V Operation Section	6
Changes to Electrical Characteristics—Mixed 5 V/3.3 V or 3.3 V/ 5 V Operation Section and Table 3	8
Changes to Table 12	15
Changes to Table 13	16
Changes to Table 13	17
Changes to Figure 8, Figure 9, Figure 10, Figure 11, Figure 12, Figure 13, Figure 14, Figure 15, Figure 16	18

7/2015—Rev. C to Rev. D

Changes to Table 5 and Table 6	12
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4/2014—Rev. B to Rev. C

Changes to Table 5	12
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2/2012—Rev. A to Rev. B

Created Hyperlink for Safety and Regulatory Approvals Entry in Features Section	1
Change to PC Board Layout Section	20

6/2007—Rev. 0 to Rev. A

Updated VDE Certification Throughout	1
Changes to Features, General Description, Note 1, Figure 1, Figure 2, and Figure 3	1
Changes to Regulatory Information Section	12
Changes to Table 7 and Figure 4 Caption	13
Added Table 10; Renumbered Sequentially	14
Added Insulation Lifetime Section	22
Inserted Figure 21, Figure 22, and Figure 23	22
Changes to Ordering Guide	23

3/2006—Revision 0: Initial Version

SPECIFICATIONS

ELECTRICAL CHARACTERISTICS—5 V OPERATION

All voltages are relative to their respective ground. $4.5\text{ V} \leq V_{DD1} \leq 5.5\text{ V}$, $4.5\text{ V} \leq V_{DD2} \leq 5.5\text{ V}$; all minimum/maximum specifications apply over the entire recommended operation range, unless otherwise noted; all typical specifications are at $T_A = 25^\circ\text{C}$, $V_{DD1} = V_{DD2} = 5\text{ V}$.

Table 1.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
DC SPECIFICATIONS						
Input Supply Current per Channel, Quiescent	$I_{DD1(Q)}$		0.57	0.83	mA	
Output Supply Current per Channel, Quiescent	$I_{DD0(Q)}$		0.29	0.35	mA	
ADuM3400, Total Supply Current, Four Channels ¹						
DC to 2 Mbps						
V_{DD1} Supply Current	$I_{DD1(Q)}$		2.9	3.5	mA	DC to 1 MHz logic signal freq.
V_{DD2} Supply Current	$I_{DD2(Q)}$		1.2	1.9	mA	DC to 1 MHz logic signal freq.
10 Mbps (BRW and CRW Grades Only)						
V_{DD1} Supply Current	$I_{DD1(10)}$		9.0	11.6	mA	5 MHz logic signal freq.
V_{DD2} Supply Current	$I_{DD2(10)}$		3.0	5.5	mA	5 MHz logic signal freq.
90 Mbps (CRW Grade Only)						
V_{DD1} Supply Current	$I_{DD1(90)}$		72	100	mA	45 MHz logic signal freq.
V_{DD2} Supply Current	$I_{DD2(90)}$		19	36	mA	45 MHz logic signal freq.
ADuM3401, Total Supply Current, Four Channels ¹						
DC to 2 Mbps						
V_{DD1} Supply Current	$I_{DD1(Q)}$		2.5	3.2	mA	DC to 1 MHz logic signal freq.
V_{DD2} Supply Current	$I_{DD2(Q)}$		1.6	2.4	mA	DC to 1 MHz logic signal freq.
10 Mbps (BRW and CRW Grades Only)						
V_{DD1} Supply Current	$I_{DD1(10)}$		7.4	10.6	mA	5 MHz logic signal freq.
V_{DD2} Supply Current	$I_{DD2(10)}$		4.4	6.5	mA	5 MHz logic signal freq.
90 Mbps (CRW Grade Only)						
V_{DD1} Supply Current	$I_{DD1(90)}$		59	82	mA	45 MHz logic signal freq.
V_{DD2} Supply Current	$I_{DD2(90)}$		32	46	mA	45 MHz logic signal freq.
ADuM3402, Total Supply Current, Four Channels ¹						
DC to 2 Mbps						
V_{DD1} or V_{DD2} Supply Current	$I_{DD1(Q)}, I_{DD2(Q)}$		2.0	2.8	mA	DC to 1 MHz logic signal freq.
10 Mbps (BRW and CRW Grades Only)						
V_{DD1} or V_{DD2} Supply Current	$I_{DD1(10)}, I_{DD2(10)}$		6.0	7.5	mA	5 MHz logic signal freq.
90 Mbps (CRW Grade Only)						
V_{DD1} or V_{DD2} Supply Current	$I_{DD1(90)}, I_{DD2(90)}$		51	62	mA	45 MHz logic signal freq.
For All Models						
Input Currents	$I_{IA}, I_{IB}, I_{IC}, I_{ID}, I_{E1}, I_{E2}$	−10	+0.01	+10	μA	$0\text{ V} \leq V_{IA}, V_{IB}, V_{IC}, V_{ID} \leq V_{DD1}$ or V_{DD2} , $0\text{ V} \leq V_{E1}, V_{E2} \leq V_{DD1}$ or V_{DD2}
Logic High Input Threshold	V_{IH}, V_{EH}	2.0			V	
Logic Low Input Threshold	V_{IL}, V_{EL}			0.8	V	
Logic High Output Voltages	$V_{OAH}, V_{OBH}, V_{OCH}, V_{ODH}$	$(V_{DD1} \text{ or } V_{DD2}) - 0.1$	5.0		V	$I_{OX} = -20\text{ μA}, V_{IX} = V_{IXH}$
		$(V_{DD1} \text{ or } V_{DD2}) - 0.4$	4.8		V	$I_{OX} = -3.2\text{ mA}, V_{IX} = V_{IXH}$
Logic Low Output Voltages	$V_{OAL}, V_{OBL}, V_{OCL}, V_{ODL}$		0.0	0.1	V	$I_{OX} = 20\text{ μA}, V_{IX} = V_{IXL}$
			0.04	0.1	V	$I_{OX} = 400\text{ μA}, V_{IX} = V_{IXL}$
			0.2	0.4	V	$I_{OX} = 3.2\text{ mA}, V_{IX} = V_{IXL}$

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
SWITCHING SPECIFICATIONS						
ARW Package						
Minimum Pulse Width ²	PW			1000	ns	C _L = 15 pF, CMOS signal levels
Maximum Data Rate ³		1			Mbps	C _L = 15 pF, CMOS signal levels
Propagation Delay ⁴	t _{PHL} , t _{PLH}	50	65	100	ns	C _L = 15 pF, CMOS signal levels
Pulse Width Distortion, t _{PLH} – t _{PHL} ⁴	PWD			40	ns	C _L = 15 pF, CMOS signal levels
Propagation Delay Skew ⁵	t _{PSK}			50	ns	C _L = 15 pF, CMOS signal levels
Channel-to-Channel Matching ⁶	t _{PSKCD/OD}			50	ns	C _L = 15 pF, CMOS signal levels
BRW Package						
Minimum Pulse Width ²	PW			100	ns	C _L = 15 pF, CMOS signal levels
Maximum Data Rate ³		10			Mbps	C _L = 15 pF, CMOS signal levels
Propagation Delay ⁴	t _{PHL} , t _{PLH}	20	32	50	ns	C _L = 15 pF, CMOS signal levels
Pulse Width Distortion, t _{PLH} – t _{PHL} ⁴	PWD			3	ns	C _L = 15 pF, CMOS signal levels
Change vs. Temperature			5		ps/°C	C _L = 15 pF, CMOS signal levels
Propagation Delay Skew ⁵	t _{PSK}			15	ns	C _L = 15 pF, CMOS signal levels
Channel-to-Channel Matching, Codirectional Channels ⁶	t _{PSKCD}			3	ns	C _L = 15 pF, CMOS signal levels
Channel-to-Channel Matching, Opposing-Directional Channels ⁶	t _{PSKOD}			6	ns	C _L = 15 pF, CMOS signal levels
CRW Package						
Minimum Pulse Width ²	PW		8.3	11.1	ns	C _L = 15 pF, CMOS signal levels
Maximum Data Rate ³		90	120		Mbps	C _L = 15 pF, CMOS signal levels
Propagation Delay ⁴	t _{PHL} , t _{PLH}	18	27	32	ns	C _L = 15 pF, CMOS signal levels
Pulse Width Distortion, t _{PLH} – t _{PHL} ⁴	PWD		0.5	2	ns	C _L = 15 pF, CMOS signal levels
Change vs. Temperature			3		ps/°C	C _L = 15 pF, CMOS signal levels
Propagation Delay Skew ⁵	t _{PSK}			10	ns	C _L = 15 pF, CMOS signal levels
Channel-to-Channel Matching, Codirectional Channels ⁶	t _{PSKCD}			2	ns	C _L = 15 pF, CMOS signal levels
Channel-to-Channel Matching, Opposing-Directional Channels ⁶	t _{PSKOD}			5	ns	C _L = 15 pF, CMOS signal levels

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
For All Models						
Output Disable Propagation Delay (High/Low-to-High Impedance)	t_{PHZ}, t_{PLH}		6	8	ns	$C_L = 15$ pF, CMOS signal levels
Output Enable Propagation Delay (High Impedance-to-High/Low)	t_{PZH}, t_{PZL}		6	8	ns	$C_L = 15$ pF, CMOS signal levels
Output Rise/Fall Time (10% to 90%)	t_R/t_F		2.5		ns	$C_L = 15$ pF, CMOS signal levels
Common-Mode Transient Immunity at Logic High Output ⁷	$ CM_H $	25	35		kV/ μ s	$V_{ix} = V_{DD1}/V_{DD2}$, $V_{CM} = 1000$ V, transient magnitude = 800 V
Common-Mode Transient Immunity at Logic Low Output ⁷	$ CM_L $	25	35		kV/ μ s	$V_{ix} = 0$ V, $V_{CM} = 1000$ V, transient magnitude = 800 V
Refresh Rate	f_r		1.2		Mbps	
Input Dynamic Supply Current per Channel ⁸	$I_{DDI(D)}$		0.20		mA/Mbps	
Output Dynamic Supply Current per Channel ⁸	$I_{DDO(D)}$		0.05		mA/Mbps	

¹ The supply current values for all four channels are combined when running at identical data rates. Output supply current values are specified with no output load present. The supply current associated with an individual channel operating at a given data rate can be calculated as described in the Power Consumption section. See Figure 8 through Figure 10 for information on per-channel supply current as a function of data rate for unloaded and loaded conditions. See Figure 11 through Figure 15 for total V_{DD1} and V_{DD2} supply currents as a function of data rate for ADuM3400/ADuM3401/ADuM3402 channel configurations.

² The minimum pulse width is the shortest pulse width at which the specified pulse width distortion is guaranteed.

³ The maximum data rate is the fastest data rate at which the specified pulse width distortion is guaranteed.

⁴ t_{PHL} propagation delay is measured from the 50% level of the falling edge of the V_{ix} signal to the 50% level of the falling edge of the V_{ox} signal. t_{PLH} propagation delay is measured from the 50% level of the rising edge of the V_{ix} signal to the 50% level of the rising edge of the V_{ox} signal.

⁵ t_{PSK} is the magnitude of the worst-case difference in t_{PHL} or t_{PLH} that is measured between units at the same operating temperature, supply voltages, and output load within the recommended operating conditions.

⁶ Codirectional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on the same side of the isolation barrier. Opposing-directional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on opposing sides of the isolation barrier.

⁷ CM_H is the maximum common-mode voltage slew rate that can be sustained while maintaining $V_O > 0.8 V_{DD2}$. CM_L is the maximum common-mode voltage slew rate that can be sustained while maintaining $V_O < 0.8$ V. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges. The transient magnitude is the range over which the common mode is slewed.

⁸ Dynamic supply current is the incremental amount of supply current required for a 1 Mbps increase in signal data rate. See Figure 8 through Figure 10 for information on per-channel supply current for unloaded and loaded conditions. See the Power Consumption section for guidance on calculating the per-channel supply current for a given data rate.

ELECTRICAL CHARACTERISTICS—3.3 V OPERATION

All voltages are relative to their respective ground. $3.0\text{ V} \leq V_{DD1} \leq 3.6\text{ V}$, $3.0\text{ V} \leq V_{DD2} \leq 3.6\text{ V}$; all minimum/maximum specifications apply over the entire recommended operation range, unless otherwise noted; all typical specifications are at $T_A = 25^\circ\text{C}$, $V_{DD1} = V_{DD2} = 3.3\text{ V}$.

Table 2.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
DC SPECIFICATIONS						
Input Supply Current per Channel, Quiescent	$I_{DD1(Q)}$		0.31	0.49	mA	
Output Supply Current per Channel, Quiescent	$I_{DDO(Q)}$		0.19	0.27	mA	
ADuM3400 , Total Supply Current, Four Channels ¹						
DC to 2 Mbps						
V_{DD1} Supply Current	$I_{DD1(Q)}$		1.6	2.1	mA	DC to 1 MHz logic signal freq.
V_{DD2} Supply Current	$I_{DD2(Q)}$		0.7	1.2	mA	DC to 1 MHz logic signal freq.
10 Mbps (BRW and CRW Grades Only)						
V_{DD1} Supply Current	$I_{DD1(10)}$		4.8	7.1	mA	5 MHz logic signal freq.
V_{DD2} Supply Current	$I_{DD2(10)}$		1.8	2.3	mA	5 MHz logic signal freq.
90 Mbps (CRW Grade Only)						
V_{DD1} Supply Current	$I_{DD1(90)}$		37	54	mA	45 MHz logic signal freq.
V_{DD2} Supply Current	$I_{DD2(90)}$		11	15	mA	45 MHz logic signal freq.
ADuM3401 , Total Supply Current, Four Channels ¹						
DC to 2 Mbps						
V_{DD1} Supply Current	$I_{DD1(Q)}$		1.4	1.9	mA	DC to 1 MHz logic signal freq.
V_{DD2} Supply Current	$I_{DD2(Q)}$		0.9	1.5	mA	DC to 1 MHz logic signal freq.
10 Mbps (BRW and CRW Grades Only)						
V_{DD1} Supply Current	$I_{DD1(10)}$		4.1	5.6	mA	5 MHz logic signal freq.
V_{DD2} Supply Current	$I_{DD2(10)}$		2.5	3.3	mA	5 MHz logic signal freq.
90 Mbps (CRW Grade Only)						
V_{DD1} Supply Current	$I_{DD1(90)}$		31	44	mA	45 MHz logic signal freq.
V_{DD2} Supply Current	$I_{DD2(90)}$		17	24	mA	45 MHz logic signal freq.
ADuM3402 , Total Supply Current, Four Channels ¹						
DC to 2 Mbps						
V_{DD1} or V_{DD2} Supply Current	$I_{DD1(Q)}, I_{DD2(Q)}$		1.2	1.7	mA	DC to 1 MHz logic signal freq.
10 Mbps (BRW and CRW Grades Only)						
V_{DD1} or V_{DD2} Supply Current	$I_{DD1(10)}, I_{DD2(10)}$		3.3	4.4	mA	5 MHz logic signal freq.
90 Mbps (CRW Grade Only)						
V_{DD1} or V_{DD2} Supply Current	$I_{DD1(90)}, I_{DD2(90)}$		24	39	mA	45 MHz logic signal freq.
For All Models						
Input Currents	$I_{IA}, I_{IB}, I_{IC}, I_{ID}, I_{E1}, I_{E2}$	-10	+0.01	+10	μA	$0\text{ V} \leq V_{IA}, V_{IB}, V_{IC}, V_{ID} \leq V_{DD1}$ or V_{DD2} , $0\text{ V} \leq V_{E1}, V_{E2} \leq V_{DD1}$ or V_{DD2}
Logic High Input Threshold	V_{IH}, V_{EH}	1.6			V	
Logic Low Input Threshold	V_{IL}, V_{EL}			0.4	V	
Logic High Output Voltages	$V_{OAH}, V_{OBH}, V_{OCH}, V_{ODH}$	$(V_{DD1} \text{ or } V_{DD2}) - 0.1$	3.0		V	$I_{OX} = -20\text{ }\mu\text{A}, V_{IX} = V_{IXH}$
		$(V_{DD1} \text{ or } V_{DD2}) - 0.4$	2.8		V	$I_{OX} = -3.2\text{ mA}, V_{IX} = V_{IXH}$
	$V_{OAL}, V_{OBL}, V_{OCL}, V_{ODL}$		0.0	0.1	V	$I_{OX} = 20\text{ }\mu\text{A}, V_{IX} = V_{IXL}$
			0.04	0.1	V	$I_{OX} = 400\text{ }\mu\text{A}, V_{IX} = V_{IXL}$
Logic Low Output Voltages				0.2	V	$I_{OX} = 3.2\text{ mA}, V_{IX} = V_{IXL}$
				0.4	V	
SWITCHING SPECIFICATIONS						
ARW Package						
Minimum Pulse Width ²	PW			1000	ns	$C_L = 15\text{ pF}$, CMOS signal levels
Maximum Data Rate ³		1			Mbps	$C_L = 15\text{ pF}$, CMOS signal levels
Propagation Delay ⁴	t_{PHL}, t_{PLH}	50	75	100	ns	$C_L = 15\text{ pF}$, CMOS signal levels

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
Pulse Width Distortion, $ t_{PLH} - t_{PHL} ^4$	PWD			40	ns	$C_L = 15$ pF, CMOS signal levels
Propagation Delay Skew ⁵	t_{PSK}			50	ns	$C_L = 15$ pF, CMOS signal levels
Channel-to-Channel Matching ⁶	$t_{PSKCD/OD}$			50	ns	$C_L = 15$ pF, CMOS signal levels
BRW Package						
Minimum Pulse Width ²	PW			100	ns	$C_L = 15$ pF, CMOS signal levels
Maximum Data Rate ³		10			Mbps	$C_L = 15$ pF, CMOS signal levels
Propagation Delay ⁴	t_{PHL}, t_{PLH}	20	38	50	ns	$C_L = 15$ pF, CMOS signal levels
Pulse Width Distortion, $ t_{PLH} - t_{PHL} ^4$	PWD			3	ns	$C_L = 15$ pF, CMOS signal levels
Change vs. Temperature			5		ps/°C	$C_L = 15$ pF, CMOS signal levels
Propagation Delay Skew ⁵	t_{PSK}			22	ns	$C_L = 15$ pF, CMOS signal levels
Channel-to-Channel Matching, Codirectional Channels ⁶	t_{PSKCD}			3	ns	$C_L = 15$ pF, CMOS signal levels
Channel-to-Channel Matching, Opposing-Directional Channels ⁶	t_{PSKOD}			6	ns	$C_L = 15$ pF, CMOS signal levels
CRW Package						
Minimum Pulse Width ²	PW		8.3	11.1	ns	$C_L = 15$ pF, CMOS signal levels
Maximum Data Rate ³		90	120		Mbps	$C_L = 15$ pF, CMOS signal levels
Propagation Delay ⁴	t_{PHL}, t_{PLH}	20	34	45	ns	$C_L = 15$ pF, CMOS signal levels
Pulse Width Distortion, $ t_{PLH} - t_{PHL} ^4$	PWD		0.5	2	ns	$C_L = 15$ pF, CMOS signal levels
Change vs. Temperature			3		ps/°C	$C_L = 15$ pF, CMOS signal levels
Propagation Delay Skew ⁵	t_{PSK}			16	ns	$C_L = 15$ pF, CMOS signal levels
Channel-to-Channel Matching, Codirectional Channels ⁶	t_{PSKCD}			2	ns	$C_L = 15$ pF, CMOS signal levels
Channel-to-Channel Matching, Opposing-Directional Channels ⁶	t_{PSKOD}			5	ns	$C_L = 15$ pF, CMOS signal levels
For All Models						
Output Disable Propagation Delay (High/Low-to-High Impedance)	t_{PHZ}, t_{PLH}		6	8	ns	$C_L = 15$ pF, CMOS signal levels
Output Enable Propagation Delay (High Impedance-to-High/Low)	t_{PZH}, t_{PZL}		6	8	ns	$C_L = 15$ pF, CMOS signal levels
Output Rise/Fall Time (10% to 90%)	t_R/t_F		3		ns	$C_L = 15$ pF, CMOS signal levels
Common-Mode Transient Immunity at Logic High Output ⁷	$ CM_H $	25	35		kV/μs	$V_{IX} = V_{DD1}/V_{DD2}$, $V_{CM} = 1000$ V, transient magnitude = 800 V
Common-Mode Transient Immunity at Logic Low Output ⁷	$ CM_L $	25	35		kV/μs	$V_{IX} = 0$ V, $V_{CM} = 1000$ V, transient magnitude = 800 V
Refresh Rate	f_r		1.1		Mbps	
Input Dynamic Supply Current per Channel ⁸	$I_{DDI(D)}$		0.10		mA/Mbps	
Output Dynamic Supply Current per Channel ⁸	$I_{DDO(D)}$		0.03		mA/Mbps	

¹ The supply current values for all four channels are combined when running at identical data rates. Output supply current values are specified with no output load present. The supply current associated with an individual channel operating at a given data rate can be calculated as described in the Power Consumption section. See Figure 8 through Figure 10 for information on per-channel supply current as a function of data rate for unloaded and loaded conditions. See Figure 11 through Figure 15 for total V_{DD1} and V_{DD2} supply currents as a function of data rate for ADuM3400/ADuM3401/ADuM3402 channel configurations.

² The minimum pulse width is the shortest pulse width at which the specified pulse width distortion is guaranteed.

³ The maximum data rate is the fastest data rate at which the specified pulse width distortion is guaranteed.

⁴ t_{PHL} propagation delay is measured from the 50% level of the falling edge of the V_{IX} signal to the 50% level of the falling edge of the V_{OX} signal. t_{PLH} propagation delay is measured from the 50% level of the rising edge of the V_{IX} signal to the 50% level of the rising edge of the V_{OX} signal.

⁵ t_{PSK} is the magnitude of the worst-case difference in t_{PHL} or t_{PLH} that is measured between units at the same operating temperature, supply voltages, and output load within the recommended operating conditions.

⁶ Codirectional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on the same side of the isolation barrier. Opposing-directional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on opposing sides of the isolation barrier.

⁷ CM_H is the maximum common-mode voltage slew rate that can be sustained while maintaining $V_O > 0.8 V_{DD2}$. CM_L is the maximum common-mode voltage slew rate that can be sustained while maintaining $V_O < 0.8$ V. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges. The transient magnitude is the range over which the common mode is slewed.

⁸ Dynamic supply current is the incremental amount of supply current required for a 1 Mbps increase in signal data rate. See Figure 8 through Figure 10 for information on per-channel supply current for unloaded and loaded conditions. See the Power Consumption section for guidance on calculating the per-channel supply current for a given data rate.

ELECTRICAL CHARACTERISTICS—MIXED 5 V/3.3 V OR 3.3 V/5 V OPERATION

All voltages are relative to their respective ground. 5 V/3.3 V operation: $4.5\text{ V} \leq V_{DD1} \leq 5.5\text{ V}$, $3.0\text{ V} \leq V_{DD2} \leq 3.6\text{ V}$; 3.3 V/5 V operation: $3.0\text{ V} \leq V_{DD1} \leq 3.6\text{ V}$, $4.5\text{ V} \leq V_{DD2} \leq 5.5\text{ V}$; all minimum/maximum specifications apply over the entire recommended operation range, unless otherwise noted; all typical specifications are at $T_A = 25^\circ\text{C}$; $V_{DD1} = 3.3\text{ V}$, $V_{DD2} = 5\text{ V}$ or $V_{DD1} = 5\text{ V}$, $V_{DD2} = 3.3\text{ V}$.

Table 3.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
DC SPECIFICATIONS						
Input Supply Current per Channel, Quiescent	$I_{DD1(Q)}$					
5 V/3.3 V Operation			0.57	0.83	mA	
3.3 V/5 V Operation			0.31	0.49	mA	
Output Supply Current per Channel, Quiescent	$I_{DDO(Q)}$					
5 V/3.3 V Operation			0.29	0.27	mA	
3.3 V/5 V Operation			0.19	0.35	mA	
ADuM3400, Total Supply Current, Four Channels¹						
DC to 2 Mbps						
V_{DD1} Supply Current	$I_{DD1(Q)}$					
5 V/3.3 V Operation			2.9	3.5	mA	DC to 1 MHz logic signal freq.
3.3 V/5 V Operation			1.6	2.1	mA	DC to 1 MHz logic signal freq.
V_{DD2} Supply Current	$I_{DD2(Q)}$					
5 V/3.3 V Operation			0.7	1.2	mA	DC to 1 MHz logic signal freq.
3.3 V/5 V Operation			1.2	1.9	mA	DC to 1 MHz logic signal freq.
10 Mbps (BRW and CRW Grades Only)						
V_{DD1} Supply Current	$I_{DD1(10)}$					
5 V/3.3 V Operation			9.0	11.6	mA	5 MHz logic signal freq.
3.3 V/5 V Operation			4.8	7.1	mA	5 MHz logic signal freq.
V_{DD2} Supply Current	$I_{DD2(10)}$					
5 V/3.3 V Operation			1.8	2.3	mA	5 MHz logic signal freq.
3.3 V/5 V Operation			3.0	5.5	mA	5 MHz logic signal freq.
90 Mbps (CRW Grade Only)						
V_{DD1} Supply Current	$I_{DD1(90)}$					
5 V/3.3 V Operation			72	100	mA	45 MHz logic signal freq.
3.3 V/5 V Operation			37	54	mA	45 MHz logic signal freq.
V_{DD2} Supply Current	$I_{DD2(90)}$					
5 V/3.3 V Operation			11	15	mA	45 MHz logic signal freq.
3.3 V/5 V Operation			19	36	mA	45 MHz logic signal freq.
ADuM3401, Total Supply Current, Four Channels¹						
DC to 2 Mbps						
V_{DD1} Supply Current	$I_{DD1(Q)}$					
5 V/3.3 V Operation			2.5	3.2	mA	DC to 1 MHz logic signal freq.
3.3 V/5 V Operation			1.4	1.9	mA	DC to 1 MHz logic signal freq.
V_{DD2} Supply Current	$I_{DD2(Q)}$					
5 V/3.3 V Operation			0.9	1.5	mA	DC to 1 MHz logic signal freq.
3.3 V/5 V Operation			1.6	2.4	mA	DC to 1 MHz logic signal freq.
10 Mbps (BRW and CRW Grades Only)						
V_{DD1} Supply Current	$I_{DD1(10)}$					
5 V/3.3 V Operation			7.4	10.6	mA	5 MHz logic signal freq.
3.3 V/5 V Operation			4.1	5.6	mA	5 MHz logic signal freq.
V_{DD2} Supply Current	$I_{DD2(10)}$					
5 V/3.3 V Operation			2.5	3.3	mA	5 MHz logic signal freq.
3.3 V/5 V Operation			4.4	6.5	mA	5 MHz logic signal freq.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
90 Mbps (CRW Grade Only)						
V _{DD1} Supply Current	I _{DD1} (90)					
5 V/3.3 V Operation			59	82	mA	45 MHz logic signal freq.
3.3 V/5 V Operation			31	44	mA	45 MHz logic signal freq.
V _{DD2} Supply Current	I _{DD2} (90)					
5 V/3.3 V Operation			17	24	mA	45 MHz logic signal freq.
3.3 V/5 V Operation			32	46	mA	45 MHz logic signal freq.
ADuM3402, Total Supply Current, Four Channels ¹						
DC to 2 Mbps						
V _{DD1} Supply Current	I _{DD1} (Q)					
5 V/3.3 V Operation			2.0	2.8	mA	DC to 1 MHz logic signal freq.
3.3 V/5 V Operation			1.2	1.7	mA	DC to 1 MHz logic signal freq.
V _{DD2} Supply Current	I _{DD2} (Q)					
5 V/3.3 V Operation			1.2	1.7	mA	DC to 1 MHz logic signal freq.
3.3 V/5 V Operation			2.0	2.8	mA	DC to 1 MHz logic signal freq.
10 Mbps (BRW and CRW Grades Only)						
V _{DD1} Supply Current	I _{DD1} (10)					
5 V/3.3 V Operation			6.0	7.5	mA	5 MHz logic signal freq.
3.3 V/5 V Operation			3.3	4.4	mA	5 MHz logic signal freq.
V _{DD2} Supply Current	I _{DD2} (10)					
5 V/3.3 V Operation			3.3	4.4	mA	5 MHz logic signal freq.
3.3 V/5 V Operation			6.0	7.5	mA	5 MHz logic signal freq.
90 Mbps (CRW Grade Only)						
V _{DD1} Supply Current	I _{DD1} (90)					
5 V/3.3 V Operation			46	62	mA	45 MHz logic signal freq.
3.3 V/5 V Operation			24	39	mA	45 MHz logic signal freq.
V _{DD2} Supply Current	I _{DD2} (90)					
5 V/3.3 V Operation			24	39	mA	45 MHz logic signal freq.
3.3 V/5 V Operation			46	62	mA	45 MHz logic signal freq.
For All Models						
Input Currents	I _{IA} , I _{IB} , I _{IC} , I _{ID} , I _{E1} , I _{E2}	-10	+0.01	+10	μA	0 V ≤ V _{IA} , V _{IB} , V _{IC} , V _{ID} ≤ V _{DD1} or V _{DD2} , 0 V ≤ V _{E1} , V _{E2} ≤ V _{DD1} or V _{DD2}
Logic High Input Threshold	V _{IH} , V _{EH}				V	
5 V/3.3 V Operation		2.0			V	
3.3 V/5 V Operation		1.6			V	
Logic Low Input Threshold	V _{IL} , V _{EL}				V	
5 V/3.3 V Operation				0.8	V	
3.3 V/5 V Operation				0.4	V	
Logic High Output Voltages	V _{OA} H, V _{OB} H, V _{OC} H, V _{OD} H	(V _{DD1} or V _{DD2}) - 0.1	(V _{DD1} or V _{DD2}) - 0.2		V	I _{OX} = -20 μA, V _{IX} = V _{IXH}
					V	I _{OX} = -3.2 mA, V _{IX} = V _{IXH}
Logic Low Output Voltages	V _{OA} L, V _{OB} L, V _{OC} L, V _{OD} L		0.0 0.04 0.2	0.1 0.1 0.4	V V V	I _{OX} = 20 μA, V _{IX} = V _{IXL} I _{OX} = 400 μA, V _{IX} = V _{IXL} I _{OX} = 3.2 mA, V _{IX} = V _{IXL}
SWITCHING SPECIFICATIONS						
ARW Package						
Minimum Pulse Width ²	PW			1000	ns	C _L = 15 pF, CMOS signal levels
Maximum Data Rate ³		1			Mbps	C _L = 15 pF, CMOS signal levels
Propagation Delay ⁴	t _{PHL} , t _{PLH}	50	70	100	ns	C _L = 15 pF, CMOS signal levels
Pulse Width Distortion, t _{PLH} - t _{PHL} ⁴	PWD			40	ns	C _L = 15 pF, CMOS signal levels
Propagation Delay Skew ⁵	t _{PSK}			50	ns	C _L = 15 pF, CMOS signal levels
Channel-to-Channel Matching ⁶	t _{PSKCD} /OD			50	ns	C _L = 15 pF, CMOS signal levels

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
BRW Package						
Minimum Pulse Width ²	PW			100	ns	C _L = 15 pF, CMOS signal levels
Maximum Data Rate ³		10			Mbps	C _L = 15 pF, CMOS signal levels
Propagation Delay ⁴	t _{PHL} , t _{PLH}	15	35	50	ns	C _L = 15 pF, CMOS signal levels
Pulse Width Distortion, t _{PLH} – t _{PHL} ⁴	PWD			3	ns	C _L = 15 pF, CMOS signal levels
Change vs. Temperature			5		ps/°C	C _L = 15 pF, CMOS signal levels
Propagation Delay Skew ⁵	t _{PSK}			22	ns	C _L = 15 pF, CMOS signal levels
Channel-to-Channel Matching, Codirectional Channels ⁶	t _{PSKCD}			3	ns	C _L = 15 pF, CMOS signal levels
Channel-to-Channel Matching, Opposing-Directional Channels ⁶	t _{PSKOD}			6	ns	C _L = 15 pF, CMOS signal levels
CRW Package						
Minimum Pulse Width ²	PW		8.3	11.1	ns	C _L = 15 pF, CMOS signal levels
Maximum Data Rate ³		90	120		Mbps	C _L = 15 pF, CMOS signal levels
Propagation Delay ⁴	t _{PHL} , t _{PLH}	20	30	40	ns	C _L = 15 pF, CMOS signal levels
Pulse Width Distortion, t _{PLH} – t _{PHL} ⁴	PWD		0.5	2	ns	C _L = 15 pF, CMOS signal levels
Change vs. Temperature			3		ps/°C	C _L = 15 pF, CMOS signal levels
Propagation Delay Skew ⁵	t _{PSK}			14	ns	C _L = 15 pF, CMOS signal levels
Channel-to-Channel Matching, Codirectional Channels ⁶	t _{PSKCD}			2	ns	C _L = 15 pF, CMOS signal levels
Channel-to-Channel Matching, Opposing-Directional Channels ⁶	t _{PSKOD}			5	ns	C _L = 15 pF, CMOS signal levels
For All Models						
Output Disable Propagation Delay (High/Low-to-High Impedance)	t _{PHZ} , t _{PLH}		6	8	ns	C _L = 15 pF, CMOS signal levels
Output Enable Propagation Delay (High Impedance-to-High/Low)	t _{PZH} , t _{PZL}		6	8	ns	C _L = 15 pF, CMOS signal levels
Output Rise/Fall Time (10% to 90%)	t _R /t _F					C _L = 15 pF, CMOS signal levels
5 V/3.3 V Operation			3.0		ns	
3.3 V/5 V Operation			2.5		ns	
Common-Mode Transient Immunity at Logic High Output ⁷	CM _H	25	35		kV/μs	V _{IX} = V _{DD1} /V _{DD2} , V _{CM} = 1000 V, transient magnitude = 800 V
Common-Mode Transient Immunity at Logic Low Output ⁷	CM _L	25	35		kV/μs	V _{IX} = 0 V, V _{CM} = 1000 V, transient magnitude = 800 V

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
Refresh Rate	f_r					
5 V/3.3 V Operation			1.2		Mbps	
3.3 V/5 V Operation			1.1		Mbps	
Input Dynamic Supply Current per Channel ⁸	$I_{DDI(D)}$					
5 V/3.3 V Operation			0.20		mA/Mbps	
3.3 V/5 V Operation			0.10		mA/Mbps	
Output Dynamic Supply Current per Channel ⁸	$I_{DDO(D)}$					
5 V/3.3 V Operation			0.03		mA/Mbps	
3.3 V/5 V Operation			0.05		mA/Mbps	

¹ The supply current values for all four channels are combined when running at identical data rates. Output supply current values are specified with no output load present. The supply current associated with an individual channel operating at a given data rate can be calculated as described in the Power Consumption section. See Figure 8 through Figure 10 for information on per-channel supply current as a function of data rate for unloaded and loaded conditions. See Figure 11 through Figure 15 for total V_{DD1} and V_{DD2} supply currents as a function of data rate for ADuM3400/ADuM3401/ADuM3402 channel configurations.

² The minimum pulse width is the shortest pulse width at which the specified pulse width distortion is guaranteed.

³ The maximum data rate is the fastest data rate at which the specified pulse width distortion is guaranteed.

⁴ t_{PHL} propagation delay is measured from the 50% level of the falling edge of the V_{ix} signal to the 50% level of the falling edge of the V_{ox} signal. t_{PLH} propagation delay is measured from the 50% level of the rising edge of the V_{ix} signal to the 50% level of the rising edge of the V_{ox} signal.

⁵ t_{PSK} is the magnitude of the worst-case difference in t_{PHL} or t_{PLH} that is measured between units at the same operating temperature, supply voltages, and output load within the recommended operating conditions.

⁶ Codirectional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on the same side of the isolation barrier. Opposing-directional channel-to-channel matching is the absolute value of the difference in propagation delays between any two channels with inputs on opposing sides of the isolation barrier.

⁷ CM_H is the maximum common-mode voltage slew rate that can be sustained while maintaining $V_O > 0.8 V_{DD2}$. CM_L is the maximum common-mode voltage slew rate that can be sustained while maintaining $V_O < 0.8 V$. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges. The transient magnitude is the range over which the common mode is slewed.

⁸ Dynamic supply current is the incremental amount of supply current required for a 1 Mbps increase in signal data rate. See Figure 8 through Figure 10 for information on per-channel supply current for unloaded and loaded conditions. See the Power Consumption section for guidance on calculating the per-channel supply current for a given data rate.

PACKAGE CHARACTERISTICS

Table 4.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
Resistance (Input-to-Output) ¹	R _{I-O}		10 ¹²		Ω	
Capacitance (Input-to-Output) ¹	C _{I-O}		2.2		pF	f = 1 MHz
Input Capacitance ²	C _I		4.0		pF	
IC Junction-to-Case Thermal Resistance, Side 1	θ _{JCI}		33		°C/W	Thermocouple located at
IC Junction-to-Case Thermal Resistance, Side 2	θ _{JCO}		28		°C/W	center of package underside

¹ Device considered a 2-terminal device; Pin 1 to Pin 8 are shorted together and Pin 9 to Pin 16 are shorted together.

² Input capacitance is from any input data pin to ground.

REGULATORY INFORMATION

The [ADuM3400/ADuM3401/ADuM3402](#) are approved by the organizations listed in Table 5. Refer to Table 10 and the Insulation Lifetime section for details regarding recommended maximum working voltages for specific cross-isolation waveforms and insulation levels.

Table 5.

UL	CSA	CQC	VDE
Recognized Under 1577 Component Recognition Program ¹	Approved under CSA Component Acceptance Notice 5A	Approved under CQC11-471543-2012	Certified according to DIN V VDE V 0884-10 (VDE V 0884-10): 2006-12 ²
Single Protection, 2500 V rms Isolation Voltage	Basic insulation per CSA 60950-1-03 and IEC 60950-1, 800 V rms (1131 V peak) maximum working voltage Reinforced insulation per CSA 60950-1-03 and IEC 60950-1, 400 V rms (566 V peak) maximum working voltage	Basic insulation per GB4943.1-2011 400 V rms (588 V peak) maximum working voltage, tropical climate, altitude ≤ 5000 meters	Reinforced insulation, 560 V peak
File E214100	File 205078	File CQC14001117249	File 2471900-4880-0001

¹ In accordance with UL 1577, each [ADuM3400/ADuM3401/ADuM3402](#) is proof tested by applying an insulation test voltage ≥ 3000 V rms for 1 sec (current leakage detection limit = 5 μA).

² In accordance with DIN V VDE V 0884-10, each [ADuM3400/ADuM3401/ADuM3402](#) is proof tested by applying an insulation test voltage ≥ 1050 V peak for 1 sec (partial discharge detection limit = 5 pC). The * marking branded on the component designates DIN V VDE V 0884-10 approval.

INSULATION AND SAFETY-RELATED SPECIFICATIONS

Table 6.

Parameter	Symbol	Value	Unit	Conditions
Rated Dielectric Insulation Voltage		2500	V rms	1-minute duration
Minimum External Air Gap (Clearance)	L(I01)	7.7 min	mm	Measured from input terminals to output terminals, shortest distance through air
Minimum External Tracking (Creepage)	L(I02)	8.1 min	mm	Measured from input terminals to output terminals, shortest distance path along body
Minimum Internal Gap (Internal Clearance)		0.017 min	mm	Insulation distance through insulation
Tracking Resistance (Comparative Tracking Index)	CTI	>400	V	DIN IEC 112/VDE 0303 Part 1
Isolation Group		II		Material Group (DIN VDE 0110, 1/89, Table 1)

DIN V VDE V 0884-10 (VDE V 0884-10) INSULATION CHARACTERISTICS

These isolators are suitable for reinforced electrical isolation only within the safety limit data. Maintenance of the safety data is ensured by protective circuits. The * marking on packages denotes DIN V VDE V 0884-10 approval.

Table 7.

Description	Conditions	Symbol	Characteristic	Unit
Installation Classification per DIN VDE 0110			I to IV	
For Rated Mains Voltage ≤ 150 V rms			I to III	
For Rated Mains Voltage ≤ 300 V rms			I to II	
For Rated Mains Voltage ≤ 400 V rms			40/105/21	
Climatic Classification			2	
Pollution Degree per DIN VDE 0110, Table 1				
Maximum Working Insulation Voltage		V_{IORM}	560	V peak
Input-to-Output Test Voltage, Method B1	$V_{IORM} \times 1.875 = V_{PR}$, 100% production test, $t_m = 1$ sec, partial discharge < 5 pC	V_{PR}	1050	V peak
Input-to-Output Test Voltage, Method A	$V_{IORM} \times 1.6 = V_{PR}$, $t_m = 60$ sec, partial discharge < 5 pC	V_{PR}		
After Environmental Tests Subgroup 1			896	V peak
After Input and/or Safety Test Subgroup 2 and Subgroup 3	$V_{IORM} \times 1.2 = V_{PR}$, $t_m = 60$ sec, partial discharge < 5 pC		672	V peak
Highest Allowable Overvoltage	Transient overvoltage, $t_{TR} = 10$ seconds	V_{TR}	4000	V peak
Safety-Limiting Values	Maximum value allowed in the event of a failure (see Figure 4)			
Case Temperature		T_S	150	°C
Side 1 Current		I_{S1}	265	mA
Side 2 Current		I_{S2}	335	mA
Insulation Resistance at T_S	$V_{IO} = 500$ V	R_S	$> 10^9$	Ω

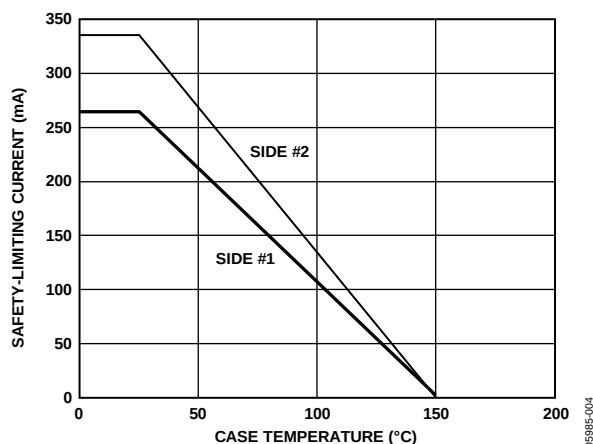


Figure 4. Thermal Derating Curve, Dependence of Safety-Limiting Values with Case Temperature per DIN V VDE V 0884-10

RECOMMENDED OPERATING CONDITIONS**Table 8.**

Parameter	Rating
Operating Temperature Range (T_A)	-40°C to $+105^\circ\text{C}$
Supply Voltages (V_{DD1} , V_{DD2}) ¹	3.0 V to 5.5 V
Input Signal Rise and Fall Times	1.0 ms

¹ All voltages are relative to their respective ground. See the DC Correctness and Magnetic Field Immunity section for information on immunity to external magnetic fields.

ABSOLUTE MAXIMUM RATINGS

Ambient temperature = 25°C, unless otherwise noted.

Table 9.

Parameter	Rating
Storage Temperature Range (T_{ST})	–65°C to +150°C
Ambient Operating Temperature Range (T_A)	–40°C to +105°C
Supply Voltages (V_{DD1} , V_{DD2}) ¹	–0.5 V to +7.0 V
Input Voltage (V_{IA} , V_{IB} , V_{IC} , V_{ID} , V_{E1} , V_{E2}) ^{1, 2}	–0.5 V to V_{DD1} + 0.5 V
Output Voltage (V_{OA} , V_{OB} , V_{OC} , V_{OD}) ^{1, 2}	–0.5 V to V_{DDO} + 0.5 V
Average Output Current per Pin ³	
Side 1 (I_{O1})	–18 mA to +18 mA
Side 2 (I_{O2})	–22 mA to +22 mA
Common-Mode Transients (CM_H , CM_L) ⁴	–100 kV/μs to +100 kV/μs

¹ All voltages are relative to their respective ground.

² V_{DD1} and V_{DDO} refer to the supply voltages on the input and output sides of a given channel, respectively. See the PC Board Layout section.

³ See Figure 4 for maximum rated current values for various temperatures.

⁴ Refers to common-mode transients across the insulation barrier. Common-mode transients exceeding the Absolute Maximum Ratings can cause latch-up or permanent damage.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device.

Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

Table 10. Maximum Continuous Working Voltage¹

Parameter	Max	Unit	Constraint
AC Voltage, Bipolar Waveform	565	V peak	50-year minimum lifetime
AC Voltage, Unipolar Waveform			
Basic Insulation	1131	V peak	Maximum approved working voltage per IEC 60950-1
Reinforced Insulation	560	V peak	Maximum approved working voltage per IEC 60950-1 and VDE V 0884-10
DC Voltage			
Basic Insulation	1131	V peak	Maximum approved working voltage per IEC 60950-1
Reinforced Insulation	560	V peak	Maximum approved working voltage per IEC 60950-1 and VDE V 0884-10

¹ Refers to continuous voltage magnitude imposed across the isolation barrier. See the Insulation Lifetime section for more details.

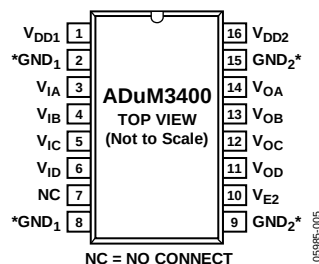
Table 11. Truth Table (Positive Logic)

V_{IX} Input ¹	V_{EX} Input ²	V_{DDI} State ¹	V_{DDO} State ¹	V_{OX} Output ¹	Notes
H	H or NC	Powered	Powered	H	Outputs return to the input state within 1 μs of V_{DDI} power restoration.
L	H or NC	Powered	Powered	L	
x	L	Powered	Powered	Z	
x	H or NC	Unpowered	Powered	H	
x	L	Unpowered	Powered	Z	Outputs return to the input state within 1 μs of V_{DDO} power restoration if V_{EX} state is H or NC. Outputs return to high impedance state within 8 ns of V_{DDO} power restoration if V_{EX} state is L.
x	x	Powered	Unpowered	Indeterminate	

¹ V_{IX} and V_{OX} refer to the input and output signals of a given channel (A, B, C, or D). V_{EX} refers to the output enable signal on the same side as the V_{OX} outputs. V_{DDI} and V_{DDO} refer to the supply voltages on the input and output sides of the given channel, respectively.

² In noisy environments, connecting V_{EX} to an external logic high or low is recommended.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

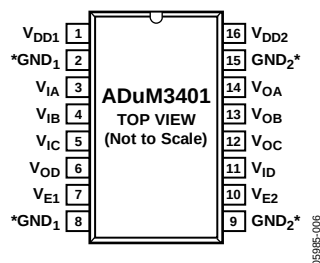


*PIN 2 AND PIN 8 ARE INTERNALLY CONNECTED AND CONNECTING BOTH TO GND₁ IS RECOMMENDED. PIN 9 AND PIN 15 ARE INTERNALLY CONNECTED AND CONNECTING BOTH TO GND₂ IS RECOMMENDED. IN NOISY ENVIRONMENTS, CONNECTING OUTPUT ENABLES (PIN 7 FOR ADuM3401/ADuM3402 AND PIN 10 FOR ALL MODELS) TO AN EXTERNAL LOGIC HIGH OR LOW IS RECOMMENDED.

Figure 5. ADuM3400 Pin Configuration

Table 12. ADuM3400 Pin Function Descriptions

Pin No.	Mnemonic	Description
1	V _{DD1}	Supply Voltage for Isolator Side 1, 3.0 V to 5.5 V.
2, 8	GND ₁	Ground 1. Ground reference for Isolator Side 1.
3	V _{IA}	Logic Input A.
4	V _{IB}	Logic Input B.
5	V _{IC}	Logic Input C.
6	V _{ID}	Logic Input D.
7	NC	No Connect.
9, 15	GND ₂	Ground 2. Ground reference for Isolator Side 2.
10	V _{E2}	Output Enable 2. Active high logic input. V _{OA} , V _{OB} , V _{OC} , and V _{OD} outputs are enabled when V _{E2} is high or disconnected. V _{OA} , V _{OB} , V _{OC} , and V _{OD} outputs are disabled when V _{E2} is low. In noisy environments, connecting V _{E2} to an external logic high or low is recommended.
11	V _{OD}	Logic Output D.
12	V _{OC}	Logic Output C.
13	V _{OB}	Logic Output B.
14	V _{OA}	Logic Output A.
16	V _{DD2}	Supply Voltage for Isolator Side 2, 3.0 V to 5.5 V.

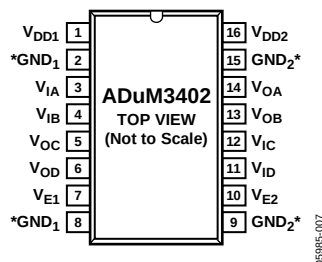


*PIN 2 AND PIN 8 ARE INTERNALLY CONNECTED AND CONNECTING BOTH TO GND₁ IS RECOMMENDED. PIN 9 AND PIN 15 ARE INTERNALLY CONNECTED AND CONNECTING BOTH TO GND₂ IS RECOMMENDED. IN NOISY ENVIRONMENTS, CONNECTING OUTPUT ENABLES (PIN 7 FOR ADuM3401/ADuM3402 AND PIN 10 FOR ALL MODELS) TO AN EXTERNAL LOGIC HIGH OR LOW IS RECOMMENDED.

Figure 6. ADuM3401 Pin Configuration

Table 13. ADuM3401 Pin Function Descriptions

Pin No.	Mnemonic	Description
1	V _{DD1}	Supply Voltage for Isolator Side 1, 3.0 V to 5.5 V.
2, 8	GND ₁	Ground 1. Ground reference for Isolator Side 1.
3	V _{IA}	Logic Input A.
4	V _{IB}	Logic Input B.
5	V _{IC}	Logic Input C.
6	V _{OD}	Logic Output D.
7	V _{E1}	Output Enable 1. Active high logic input. V _{OD} output is enabled when V _{E1} is high or disconnected. V _{OD} is disabled when V _{E1} is low. In noisy environments, connecting V _{E1} to an external logic high or low is recommended.
9, 15	GND ₂	Ground 2. Ground reference for Isolator Side 2.
10	V _{E2}	Output Enable 2. Active high logic input. V _{OA} , V _{OB} , and V _{OC} outputs are enabled when V _{E2} is high or disconnected. V _{OA} , V _{OB} , and V _{OC} outputs are disabled when V _{E2} is low. In noisy environments, connecting V _{E2} to an external logic high or low is recommended.
11	V _{ID}	Logic Input D.
12	V _{OC}	Logic Output C.
13	V _{OB}	Logic Output B.
14	V _{OA}	Logic Output A.
16	V _{DD2}	Supply Voltage for Isolator Side 2, 3.0 V to 5.5 V.



*PIN 2 AND PIN 8 ARE INTERNALLY CONNECTED AND CONNECTING BOTH TO GND₁ IS RECOMMENDED. PIN 9 AND PIN 15 ARE INTERNALLY CONNECTED AND CONNECTING BOTH TO GND₂ IS RECOMMENDED. IN NOISY ENVIRONMENTS, CONNECTING OUTPUT ENABLES (PIN 7 FOR ADuM3401/ADuM3402 AND PIN 10 FOR ALL MODELS) TO AN EXTERNAL LOGIC HIGH OR LOW IS RECOMMENDED.

Figure 7. ADuM3402 Pin Configuration

Table 14. ADuM3402 Pin Function Descriptions

Pin No.	Mnemonic	Description
1	V _{DD1}	Supply Voltage for Isolator Side 1, 3.0 V to 5.5 V.
2, 8	GND ₁	Ground 1. Ground reference for Isolator Side 1.
3	V _{IA}	Logic Input A.
4	V _{IB}	Logic Input B.
5	V _{OC}	Logic Output C.
6	V _{OD}	Logic Output D.
7	V _{E1}	Output Enable 1. Active high logic input. V _{OC} and V _{OD} outputs are enabled when V _{E1} is high or disconnected. V _{OC} and V _{OD} outputs are disabled when V _{E1} is low. In noisy environments, connecting V _{E1} to an external logic high or low is recommended.
9, 15	GND ₂	Ground 2. Ground reference for Isolator Side 2.
10	V _{E2}	Output Enable 2. Active high logic input. V _{OA} and V _{OB} outputs are enabled when V _{E2} is high or disconnected. V _{OA} and V _{OB} outputs are disabled when V _{E2} is low. In noisy environments, connecting V _{E2} to an external logic high or low is recommended.
11	V _{ID}	Logic Input D.
12	V _{IC}	Logic Input C.
13	V _{OB}	Logic Output B.
14	V _{OA}	Logic Output A.
16	V _{DD2}	Supply Voltage for Isolator Side 2, 3.0 V to 5.5 V.

TYPICAL PERFORMANCE CHARACTERISTICS

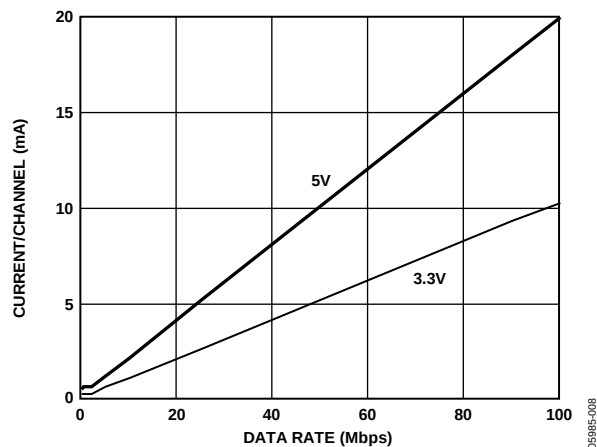


Figure 8. Typical Input Supply Current per Channel vs. Data Rate (No Load)

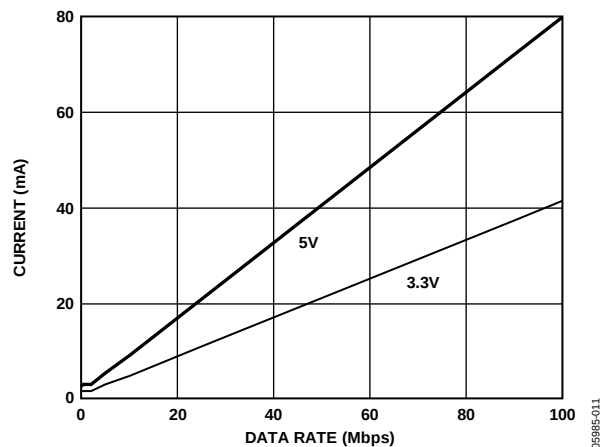
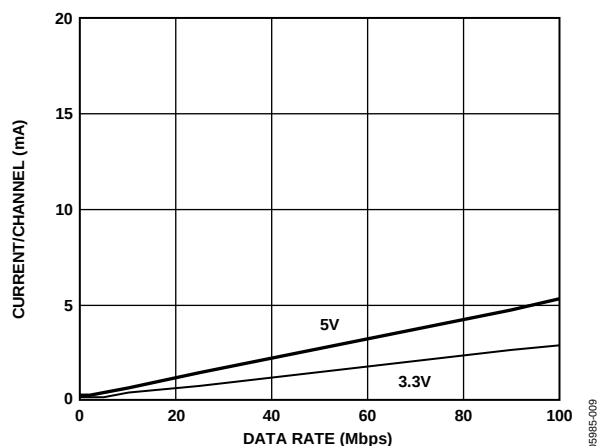
Figure 11. Typical ADuM3400 V_{DD1} Supply Current vs. Data Rate for 5 V and 3.3 V Operation

Figure 9. Typical Output Supply Current per Channel vs. Data Rate (No Load)

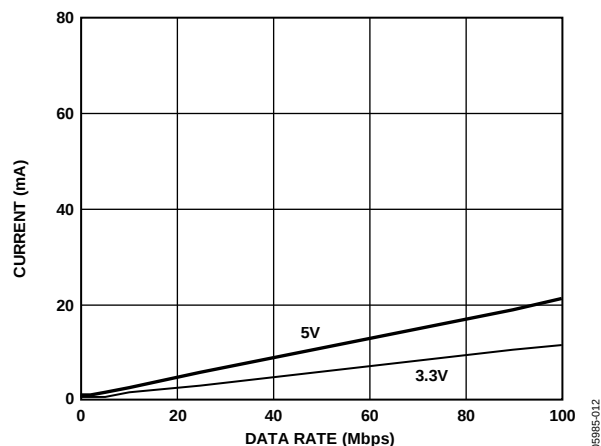
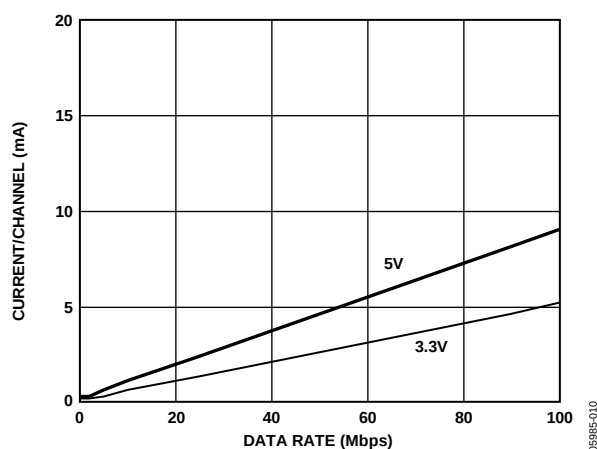
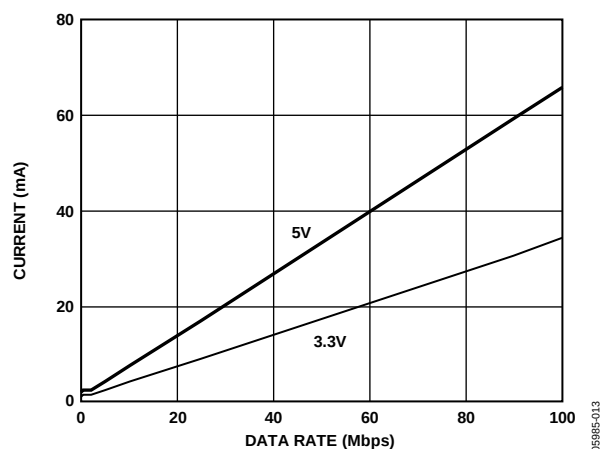
Figure 12. Typical ADuM3400 V_{DD2} Supply Current vs. Data Rate for 5 V and 3.3 V Operation

Figure 10. Typical Output Supply Current per Channel vs. Data Rate (15 pF Output Load)

Figure 13. Typical ADuM3401 V_{DD1} Supply Current vs. Data Rate for 5 V and 3.3 V Operation

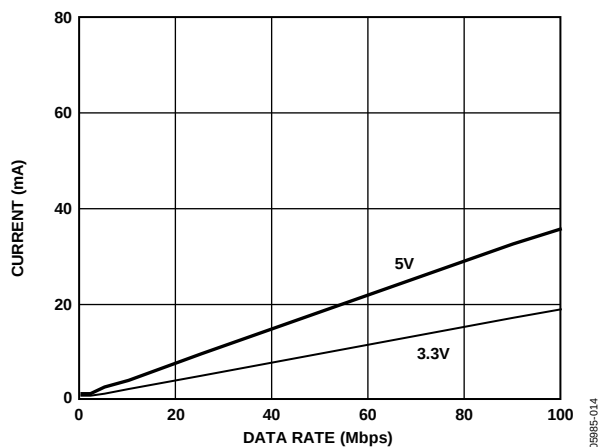


Figure 14. Typical ADuM3401 V_{DD2} Supply Current vs. Data Rate for 5 V and 3.3 V Operation

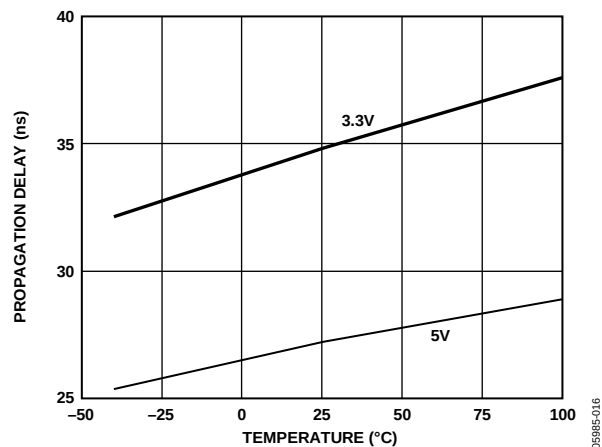


Figure 16. Propagation Delay vs. Temperature, C Grade

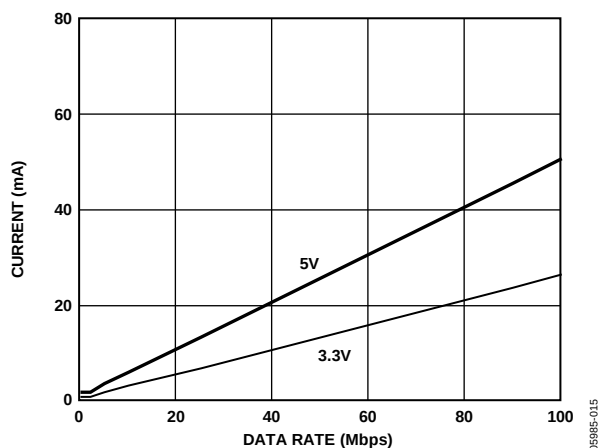


Figure 15. Typical ADuM3402 V_{DD1} or V_{DD2} Supply Current vs. Data Rate for 5 V and 3.3 V Operation

APPLICATION INFORMATION

PC BOARD LAYOUT

The ADuM3400/ADuM3401/ADuM3402 digital isolators require no external interface circuitry for the logic interfaces. Power supply bypassing is strongly recommended at the input and output supply pins (see Figure 17). Bypass capacitors are most conveniently connected between Pin 1 and Pin 2 for V_{DD1} and between Pin 15 and Pin 16 for V_{DD2} . The capacitor value must be between 0.01 μ F and 0.1 μ F. The total lead length between both ends of the capacitor and the input power supply pin must not exceed 20 mm. Bypassing between Pin 1 and Pin 8 and between Pin 9 and Pin 16 must also be considered unless the ground pair on each package side is connected close to the package.

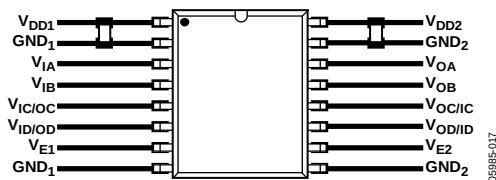


Figure 17. Recommended Printed Circuit Board Layout

In applications involving high common-mode transients, care must be taken to ensure that board coupling across the isolation barrier is minimized. Furthermore, the board layout must be designed such that any coupling that does occur equally affects all pins on a given component side. Failure to ensure this can cause voltage differentials between pins exceeding the Absolute Maximum Ratings of the device, thereby leading to latch-up or permanent damage.

See the AN-1109 Application Note for board layout guidelines.

SYSTEM-LEVEL ESD CONSIDERATIONS AND ENHANCEMENTS

System-level ESD reliability (for example, per IEC 61000-4-x) is highly dependent on system design, which varies widely by application. The ADuM3400/ADuM3401/ADuM3402 incorporate many enhancements to make ESD reliability less dependent on system design. The enhancements include:

- ESD protection cells added to all input/output interfaces.
- Key metal trace resistances reduced using wider geometry and paralleling of lines with vias.
- The SCR effect inherent in CMOS devices minimized by use of guarding and isolation technique between PMOS and NMOS devices.
- Areas of high electric field concentration eliminated using 45° corners on metal traces.
- Supply pin overvoltage prevented with larger ESD clamps between each supply pin and respective ground.

While the ADuM3400/ADuM3401/ADuM3402 improve system-level ESD reliability, they are no substitute for a robust system-level design. See the AN-793 Application Note, *ESD/Latch-Up Considerations with iCoupler Isolation Products* for detailed recommendations on board layout and system-level design.

PROPAGATION DELAY-RELATED PARAMETERS

Propagation delay is a parameter that describes the time it takes a logic signal to propagate through a component. The propagation delay to a logic low output can differ from the propagation delay to a logic high.

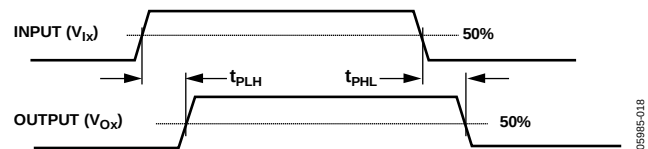


Figure 18. Propagation Delay Parameters

Pulse width distortion is the maximum difference between these two propagation delay values and is an indication of how accurately the input signal timing is preserved.

Channel-to-channel matching refers to the maximum amount the propagation delay differs between channels within a single ADuM3400/ADuM3401/ADuM3402 component.

Propagation delay skew refers to the maximum amount the propagation delay differs between multiple ADuM3400/ADuM3401/ADuM3402 components operating under the same conditions.

DC CORRECTNESS AND MAGNETIC FIELD IMMUNITY

Positive and negative logic transitions at the isolator input cause narrow (~1 ns) pulses to be sent to the decoder via the transformer. The decoder is bistable and is, therefore, either set or reset by the pulses, indicating input logic transitions. In the absence of logic transitions at the input for more than ~1 μ s, a periodic set of refresh pulses indicative of the correct input state are sent to ensure dc correctness at the output. If the decoder receives no internal pulses of more than about 5 μ s, the input side is assumed to be unpowered or nonfunctional, in which case the isolator output is forced to a default state (see Table 11) by the watchdog timer circuit.

The limitation on the magnetic field immunity of the ADuM3400/ADuM3401/ADuM3402 is set by the condition in which induced voltage in the receiving coil of the transformer is sufficiently large to either falsely set or reset the decoder. The following analysis defines the conditions under which this can occur. The 3.3 V operating condition of the ADuM3400/ADuM3401/ADuM3402 is examined because it represents the most susceptible mode of operation.

The pulses at the transformer output have an amplitude greater than 1.0 V. The decoder has a sensing threshold at about 0.5 V, thus establishing a 0.5 V margin in which induced voltages can be tolerated. The voltage induced across the receiving coil is given by

$$V = (-d\beta/dt)\sum r_n^2; N = 1, 2, \dots, N$$

where:

β is magnetic flux density (gauss).

N is the number of turns in the receiving coil.

r_n is the radius of the n^{th} turn in the receiving coil (cm).

Given the geometry of the receiving coil in the [ADuM3400/ADuM3401/ADuM3402](#) and an imposed requirement that the induced voltage be at most 50% of the 0.5 V margin at the decoder, a maximum allowable magnetic field is calculated as shown in Figure 19.

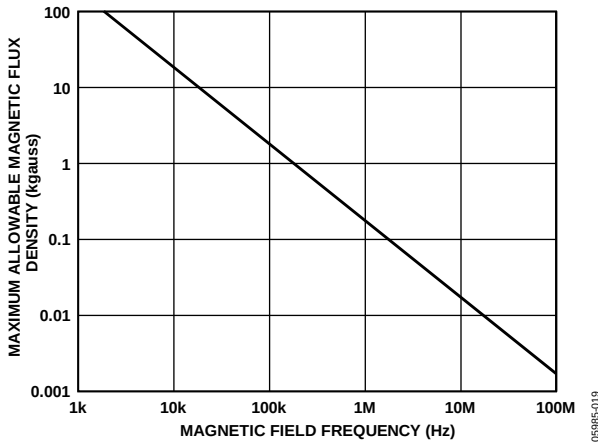


Figure 19. Maximum Allowable External Magnetic Flux Density

For example, at a magnetic field frequency of 1 MHz, the maximum allowable magnetic field of 0.2 kgauss induces a voltage of 0.25 V at the receiving coil, which is about 50% of the sensing threshold and does not cause a faulty output transition. Similarly, if such an event occurs during a transmitted pulse (and is of the worst-case polarity), it reduces the received pulse from >1.0 V to 0.75 V—still well above the 0.5 V sensing threshold of the decoder.

The preceding magnetic flux density values correspond to specific current magnitudes at given distances from the [ADuM3400/ADuM3401/ADuM3402](#) transformers. Figure 20 expresses these allowable current magnitudes as a function of frequency for selected distances. As shown, the [ADuM3400/ADuM3401/ADuM3402](#) are extremely immune and can be affected only by extremely large currents operated at high frequency very close to the component. For the 1 MHz example noted, place a 0.5 kA current 5 mm away from the [ADuM3400/ADuM3401/ADuM3402](#) to affect the operation of the component.

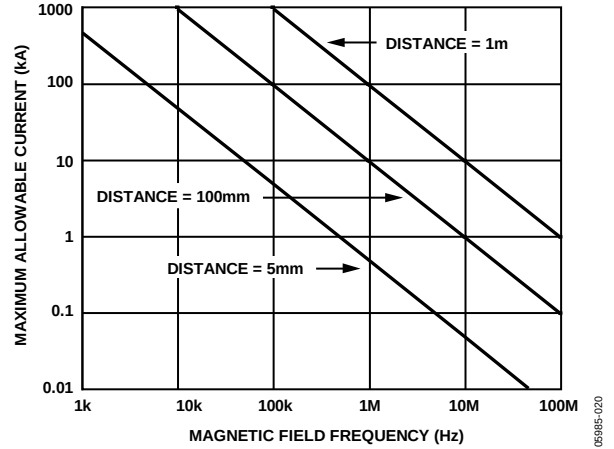


Figure 20. Maximum Allowable Current for Various Current-to-ADuM3400/ADuM3401/ADuM3402 Spacings

Note that at combinations of strong magnetic field and high frequency, any loops formed by printed circuit board traces can induce error voltages sufficiently large enough to trigger the thresholds of succeeding circuitry. Care must be taken in the layout of such traces to avoid this possibility.

POWER CONSUMPTION

The supply current at a given channel of the [ADuM3400/ADuM3401/ADuM3402](#) isolator is a function of the supply voltage, the channel data rate, and the channel output load.

For each input channel, the supply current is given by

$$I_{DDI} = I_{DDI(Q)} \quad f \leq 0.5 f_r$$

$$I_{DDI} = I_{DDI(D)} \times (2f - f_r) + I_{DDI(Q)} \quad f > 0.5 f_r$$

For each output channel, the supply current is given by

$$I_{DDO} = I_{DDO(Q)} \quad f \leq 0.5 f_r$$

$$I_{DDO} = (I_{DDO(D)} + (0.5 \times 10^{-3}) \times C_L \times V_{DDO}) \times (2f - f_r) + I_{DDO(Q)} \quad f > 0.5 f_r$$

where:

$I_{DDI(D)}$, $I_{DDO(D)}$ are the input and output dynamic supply currents per channel (mA/Mbps).

C_L is the output load capacitance (pF).

V_{DDO} is the output supply voltage (V).

f is the input logic signal frequency (MHz); it is half of the input data rate expressed in units of Mbps.

f_r is the input stage refresh rate (Mbps).

$I_{DDI(Q)}$, $I_{DDO(Q)}$ are the specified input and output quiescent supply currents (mA).

To calculate the total I_{DD1} and I_{DD2} supply current, the supply currents for each input and output channel corresponding to V_{DD1} and V_{DD2} are calculated and totaled. Figure 8 provides the per-channel input supply current as a function of the data rate. Figure 9 and Figure 10 provide the per-channel supply output current as a function of the data rate for an unloaded output condition and for a 15 pF output condition, respectively. Figure 11 through Figure 15 provide the total V_{DD1} and V_{DD2} supply current as a function of the data rate for the [ADuM3400/ADuM3401/ADuM3402](#) channel configurations.

INSULATION LIFETIME

All insulation structures eventually break down when subjected to voltage stress over a sufficiently long period. The rate of insulation degradation is dependent on the characteristics of the voltage waveform applied across the insulation. In addition to the testing performed by the regulatory agencies, Analog Devices carries out an extensive set of evaluations to determine the lifetime of the insulation structure within the [ADuM3400/ADuM3401/ADuM3402](#).

Analog Devices performs accelerated life testing using voltage levels higher than the rated continuous working voltage. Acceleration factors for several operating conditions are determined. These factors allow calculation of the time to failure at the actual working voltage. The values shown in Figure 21 summarize the peak voltage for 50 years of service life for a bipolar ac operating condition, and the maximum CSA/VDE approved working voltages. In many cases, the approved working voltage is higher than the 50-year service life voltage. Operation at these high working voltages can lead to shortened insulation life in some cases.

The insulation lifetime of the [ADuM3400/ADuM3401/ADuM3402](#) depends on the voltage waveform type imposed across the isolation barrier. The *iCoupler* insulation structure degrades at different rates depending on whether the waveform is bipolar ac, unipolar ac, or dc. Figure 21, Figure 22, and Figure 23 illustrate these different isolation voltage waveforms.

Bipolar ac voltage is the most stringent environment. The goal of a 50-year operating lifetime under the ac bipolar condition determines the recommended maximum working voltage of Analog Devices.

In the case of unipolar ac or dc voltage, the stress on the insulation is significantly lower, which allows operation at higher working voltages while still achieving a 50-year service life. The working voltages listed in Table 10 can be applied while maintaining the 50-year minimum lifetime provided the voltage conforms to either the unipolar ac or dc voltage cases. Any cross insulation voltage waveform that does not conform to Figure 22 or Figure 23 must be treated as a bipolar ac waveform and the peak voltage must be limited to the 50-year lifetime voltage value listed in Table 10.

Note that the voltage presented in Figure 22 is shown as sinusoidal for illustration purposes only. It is meant to represent any voltage waveform varying between 0 V and some limiting value. The limiting value can be positive or negative, but the voltage cannot cross 0 V.

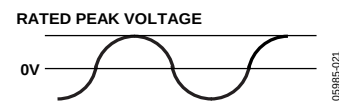


Figure 21. Bipolar AC Waveform

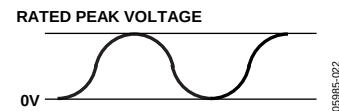


Figure 22. Unipolar AC Waveform

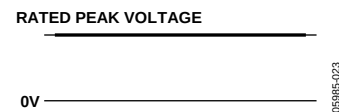
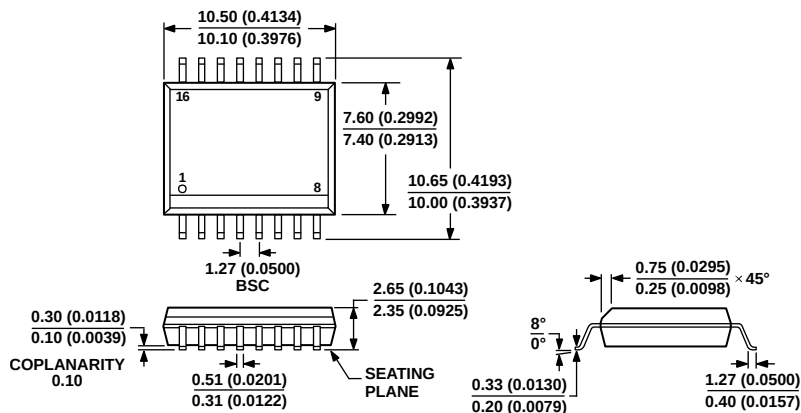


Figure 23. DC Waveform

OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MS-013-AA
CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS
(IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR
REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

03-27-2007-B

Figure 24. 16-Lead Standard Small Outline Package [SOIC_W]
Wide Body (RW-16)
Dimensions shown in millimeters and (inches)

ORDERING GUIDE

Model ^{1,2}	Number of Inputs, V _{DD1} Side	Number of Inputs, V _{DD2} Side	Maximum Data Rate (Mbps)	Maximum Propagation Delay, 5 V (ns)	Maximum Pulse Width Distortion (ns)	Temperature Range	Package Description	Package Option
ADuM3400ARWZ	4	0	1	100	40	−40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM3400BRWZ	4	0	10	50	3	−40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM3400CRWZ	4	0	90	32	2	−40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM3401ARWZ	3	1	1	100	40	−40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM3401BRWZ	3	1	10	50	3	−40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM3401CRWZ	3	1	90	32	2	−40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM3402ARWZ	2	2	1	100	40	−40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM3402BRWZ	2	2	10	50	3	−40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM3402CRWZ	2	2	90	32	2	−40°C to +105°C	16-Lead SOIC_W	RW-16

¹ Z = RoHS Compliant Part.

² Tape and reel are available. The addition of an -RL suffix designates a 13" (1,000 units) tape-and-reel option.

NOTES

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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